

REMARKS

This application has been carefully reviewed in light of the Office Action dated March 10, 2004. Claims 11 to 21 are in the application, with Claims 11 and 17 being the independent claims. Claims 1 to 10 have been cancelled without prejudice to or disclaimer of the subject matter presented therein; and Claims 11 to 21 have been newly-added. Reconsideration and further examination are respectfully requested.

A new title of the invention has been provided. In a telephone conversation with Applicants' representative, the Examiner indicated that this title would be acceptable.

The specification has been amended to attend to formal matters.

Applicants gratefully acknowledge the indication the Claims 2, 3 and 5 contain allowable subject matter. New Claim 11 contains the allowable subject matter of Claim 2. Accordingly, Claim 11, together with dependent Claims 12 to 16, is believed to be in condition for allowance.

Claims 1, 7 and 8 were rejected under 35 U.S.C. § 102(b) over U.S. Patent No. 5,757,456 (Yamazaki); and Claims 1, 4, 6 and 9 were rejected under 35 U.S.C. § 103(a) over Yamazaki in view of U.S. Patent No. 6,627,487 (Zhang). The rejections are respectfully traversed.

According to one feature of the invention as recited by new Claim 17, a separation layer is formed in the semiconductor substrate by implanting ions in the semiconductor substrate through the surface of the semiconductor substrate.

Yamazaki is not seen to teach or suggest at least the foregoing feature.

As described at col. 7, lines 11 to 18, of Yamazaki, N-type regions 39 and P-type regions 40 are formed by implanting ions into silicon islands 34 and 35. See Figs. 4A and 4B. However, nowhere is Yamazaki seen to disclose that his separation layer 32 is formed in a semiconductor substrate by implanting ions in the semiconductor substrate through the surface of the semiconductor substrate.

Zhang is not seen to remedy the foregoing deficiency of Yamazaki.

Applicants therefore conclude that the applied documents do not teach or suggest the claimed invention, and it is respectfully requested that the Section 102 and 103 rejections be withdrawn.

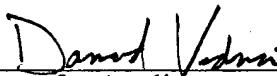
An Information Disclosure Statement was filed on May 25, 2004.

Consideration of the documents cited therein is respectfully requested.

No other matters being raised, the entire application is believed to be fully in condition for allowance, and such action is courteously solicited.

Applicants' undersigned attorney may be reached in our Washington, D.C. office by telephone at (202) 530-1010. All correspondence should continue to be directed to our address given below.

Respectfully submitted,

  
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